IN THE SPECIFICATION

Please replace the paragraph beginning on page 4, line 17 with the following paragraph:

The apparatus comprises a shielding plate within a plasma reactor to regulate the material process. The term plasma-assisted material process will be used interchangeably with the terms plasma-assisted etching process and plasma enhanced chemical vapor deposition ~~(PEVCD)~~ (PECVD). Further, these terms may be abbreviated to etching and deposition. In other words, the apparatus is not limited to etching processes. The term plasma reactor will be used to mean an inductively coupled plasma reactor or other plasma reactor. The plate can regulate ion flux across the substrate during an etch process. Ion flux is the quantity of ions diffusing through and perpendicular to a unit cross-sectional area (i.e., the substrate) per unit time. An ion is an atom or molecule with a positive charge because electrons have been removed or a negative charge because electrons have been added. Negative ions do not diffuse to the chamber wall and substrate because of the electrostatic field in plasma. A plasma is a discharged gas in which some individual atoms are ionized though the total number of positive and negative charges is equal, maintaining an overall electrical neutrality.

Please replace the paragraph beginning on page 8, line 11 with the following paragraph:

Fig. 3 is an illustration of a cross-section of plasma densities for various embodiments of plate usage, in accordance with the present invention. Plasma density is synonymous to electron density. Plasma densities are measured in number of ions / cm^3 at 4 mTorr Ar and 600 W of ICP radio frequency power. In the case A embodiment, there was no disk ~~was~~ in the plasma chamber. In the case B embodiment, a 2-cm radius disk was placed at a height of 5 cm above the reticle. In the case C embodiment, a 4-cm radius disk was placed at 5 cm above the reticle. In the case D embodiment, a 4-cm radius disk was placed at 11 cm above the reticle. In the case E embodiment, a hollow disk, or disk with a radial cutout, having a 10-cm outer radius and a 5-cm inner radius was placed at a height of 5 cm above the reticle. The projected density contour lines changed significantly in situations where a disk was present in the chamber. In embodiments B, C, and D where solid disks were used, plasma density in the central area of the reticle was suppressed. In the case E embodiment, a hollow disk suppressed the density at the outer edges of the reticle, because plasma can penetrate the hole in the disk. In yet another embodiment, the location of the disk is altered depending upon changes in chamber pressure or other variables.